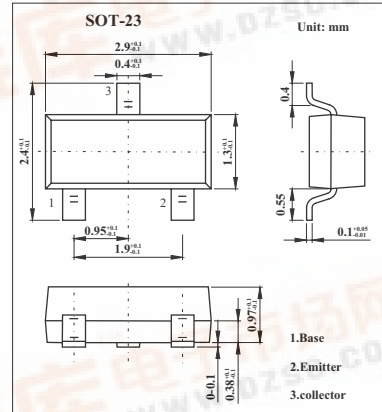


SMD Type Transistors

Medium Power Transistor
FM549A

- Features
- Low equivalent on-resistance.



■ Absolute Maximum Ratings Ta = 25°C

| Parameter | Symbol | Rating | Unit |
|---|-----------------------------------|-------------|------|
| Collector-base voltage | V _{CB0} | -35 | V |
| Collector-emitter voltage | V _{CE0} | -30 | V |
| Emitter-base voltage | V _{EB0} | -5 | V |
| Peak collector current | I _{CM} | -2 | A |
| Collector current | I _C | -1 | A |
| Base current | I _B | -200 | mA |
| Power dissipation | P _{tot} | 500 | mW |
| Operating and storage temperature range | T _j , T _{stg} | -55 to +150 | °C |

FMMT549A

■ Electrical Characteristics Ta = 25°C

| Parameter | Symbol | Testconditons | Min | Typ | Max | Unit |
|--|----------------------|--|-----|-------|-------|------|
| Collector-base breakdown voltage | V _{(BR)CBO} | I _C =-100μA | -35 | | | V |
| Collector-emitter breakdown voltage * | V _{(BR)CEO} | I _C =-10mA | -30 | | | V |
| Emitter-base breakdown voltage | V _{(BR)EBO} | I _E =-100μA | -5 | | | V |
| Collector cutoff current | I _{CBO} | V _{CB} =-30V | | | -0.1 | μA |
| Emitter cut-off current | I _{EBO} | V _{EB} =-4V | | | -0.1 | μA |
| Collector-emitter saturation voltage * | V _{CE(sat)} | I _C =-100mA, I _B =-1A | | | -0.3 | V |
| Base-emitter saturation voltage * | V _{BE(sat)} | I _C =-1A, I _B =-100mA | | -0.9 | -1.25 | V |
| Base-emitter voltage * | V _{BE(ON)} | I _C =-1A, V _{CE} =-2V | | -0.85 | -1 | V |
| DC current gain * | h _{FE} | I _C =-50mA, V _{CE} =-2V | 70 | 200 | | |
| | | I _C =-1A, V _{CE} =-2V | 80 | 130 | | |
| | | I _C =-2A, V _{CE} =-2V | 40 | 80 | | |
| | | I _C =-500mA, V _{CE} =-2V | 150 | 200 | 500 | |
| Current-gain-bandwidth product | f _T | I _C =-100mA, V _{CE} =-5V, f=100MHz | 100 | | | MHz |
| Output capacitance | C _{obo} | V _{CB} =-10V, f=1MHz | | | 25 | pF |
| Switching times | t _{on} | V _{CB} =-10V, f=1MHz | | 50 | | ns |
| | t _{off} | I _C =-500mA, V _{CC} =-10V, I _{B1} =I _{B2} =-50mA | | 300 | | ns |

* Pulse test: t_p ≤ 300 μs; d ≤ 0.02.

■ Marking

| | |
|---------|-----|
| Marking | 59A |
|---------|-----|